

isc Silicon NPN Darlington Power Transistor

BD901

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 100V(Min)
- · High DC Current Gain
 - : h_{FE}= 750(Min) @I_C= 3A
- · Collector Power Dissipation-
 - : Pc= 70W@ Tc= 25°C
- 8 A Continuous Collector Current
- Complement to Type BD902
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



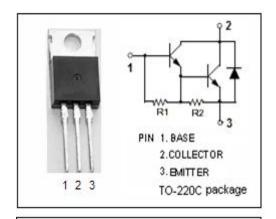
 Designed for use as complementary AF push-pull output stage applications

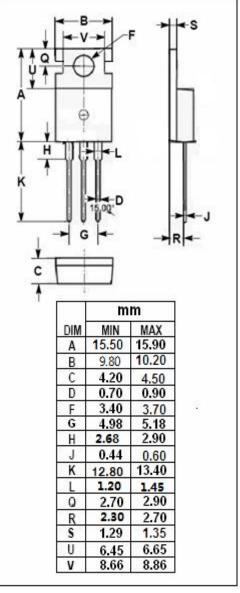
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|---------|------------|--|
| V _{CBO} | Collector-Base Voltage | 100 | V | |
| V _{CEO} | Collector-Emitter Voltage | 100 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current-Continuous | 8 | Α | |
| I _B | Base Current-Continuous | 0.3 | Α | |
| Pc | Collector Power Dissipation @ T _a =25°C | 2 | W | |
| | Collector Power Dissipation @ T _C =25℃ | 70 | | |
| TJ | Junction Temperature | 150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 1.79 | °C/W |
| R _{th j-a} | Rth j-a Thermal Resistance, Junction to Ambient | | °C/W |







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ELECTRICAL CHARACTERISTICS

 T_{C} =25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 50mA; I _B = 0 | 100 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 3A; I _B = 12mA | | | 2.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | Ic= 3A; Vc= 3V | | | 2.5 | V |
| Ісво | Collector Cutoff Current | V _{CB} = 100V; I _E = 0 | | | 0.2 | - mA |
| | | V _{CB} = 100V; I _E = 0; T _C = 100°C | | | 2.0 | |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 50V; I _B = 0 | | | 0.5 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 2 | mA |
| h _{FE} | DC Current Gain | Ic= 3A; Vc== 3V | 750 | | | |

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